

MOS FIELD EFFECT TRANSISTOR

2SK3456

SWITCHING

N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3456 is N-channel DMOS FET device that features a low gate charge and excellent switching characteristics, designed for high voltage applications such as switching power supply, AC adapter.

FEATURES

- Low gate charge
 $Q_G = 30 \text{ nC TYP. (} V_{DD} = 400 \text{ V, } V_{GS} = 10 \text{ V, } I_D = 12 \text{ A)}$
- Gate voltage rating $\pm 30 \text{ V}$
- Low on-state resistance
 $R_{DS(on)} = 0.60 \text{ } \Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 6.0 \text{ A)}$
- Avalanche capability ratings
- Surface mount package available

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3456	TO-220AB
2SK3456-S	TO-262
2SK3456-ZJ	TO-263

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	500	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 30	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 12	A
Drain Current (Pulse) ^{Note1}	$I_{D(pulse)}$	± 36	A
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T1}	1.5	W
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T2}	100	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Single Avalanche Current ^{Note2}	I_{AS}	12	A
Single Avalanche Energy ^{Note2}	E_{AS}	103	mJ

Notes 1. $PW \leq 10 \text{ } \mu\text{s}$, Duty Cycle $\leq 1\%$

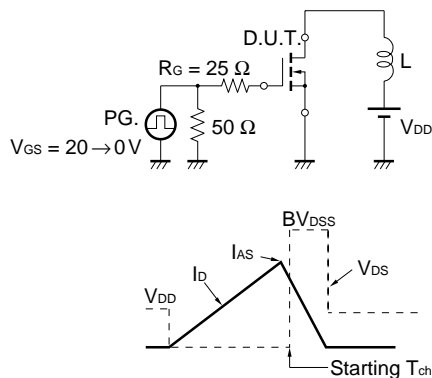
2. Starting $T_{ch} = 25^\circ\text{C}$, $V_{DD} = 150 \text{ V}$, $R_G = 25 \text{ } \Omega$, $V_{GS} = 20 \rightarrow 0 \text{ V}$

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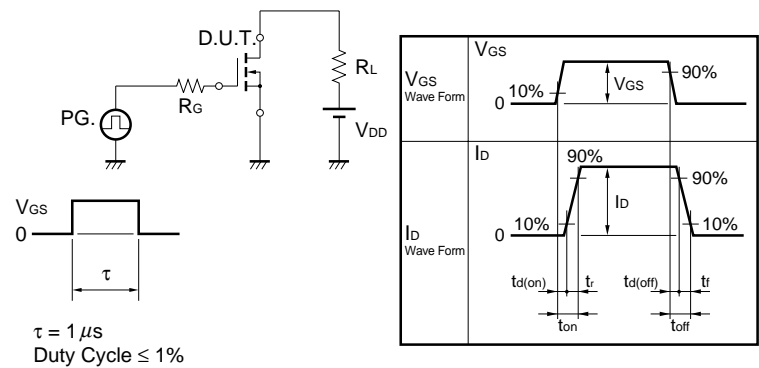
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$			100	μA
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$			± 100	nA
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.5		3.5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 6.0\text{ A}$	2.0			S
Drain to Source On-state Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}$		0.48	0.60	Ω
Input Capacitance	C_{iss}	$V_{DS} = 10\text{ V}$		1620		pF
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$		250		pF
Reverse Transfer Capacitance	C_{rss}	$f = 1\text{ MHz}$		10		pF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 150\text{ V}, I_D = 6.0\text{ A}$		24		ns
Rise Time	t_r	$V_{GS} = 10\text{ V}$		18		ns
Turn-off Delay Time	$t_{d(off)}$	$R_G = 10\ \Omega$		50		ns
Fall Time	t_f			15		ns
Total Gate Charge	Q_G	$V_{DD} = 400\text{ V}$		30		nC
Gate to Source Charge	Q_{GS}	$V_{GS} = 10\text{ V}$		9		nC
Gate to Drain Charge	Q_{GD}	$I_D = 12\text{ A}$		11		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	$I_F = 12\text{ A}, V_{GS} = 0\text{ V}$		1.0		V
Reverse Recovery Time	t_{rr}	$I_F = 12\text{ A}, V_{GS} = 0\text{ V}$		1.5		μs
Reverse Recovery Charge	Q_{rr}	$di/dt = 50\text{ A}/\mu\text{s}$		11		μC

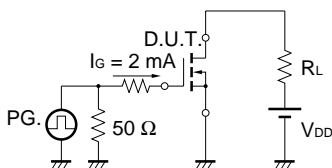
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

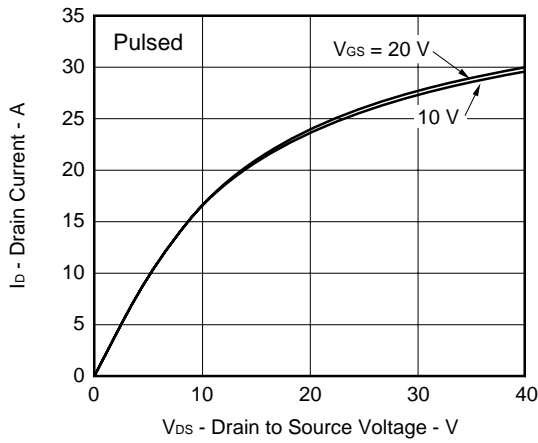


TEST CIRCUIT 3 GATE CHARGE

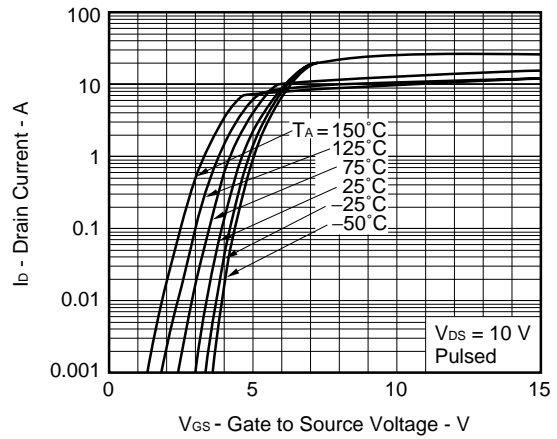


TYPICAL CHARACTERISTICS (T_A = 25°C)

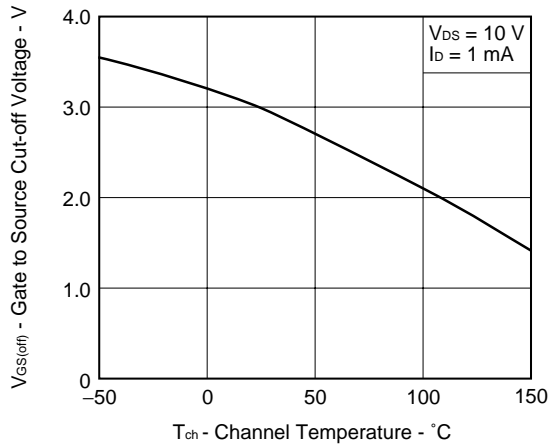
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



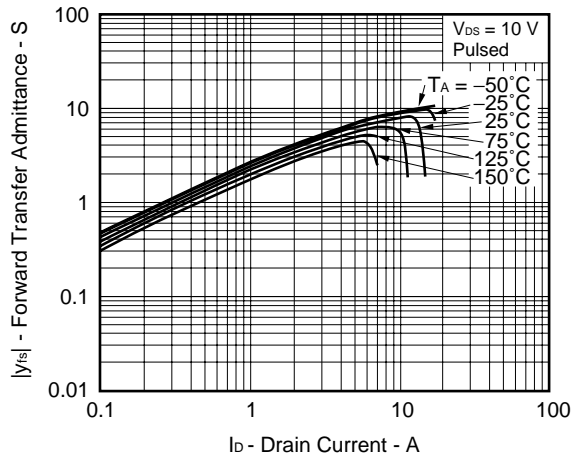
FORWARD TRANSFER CHARACTERISTICS



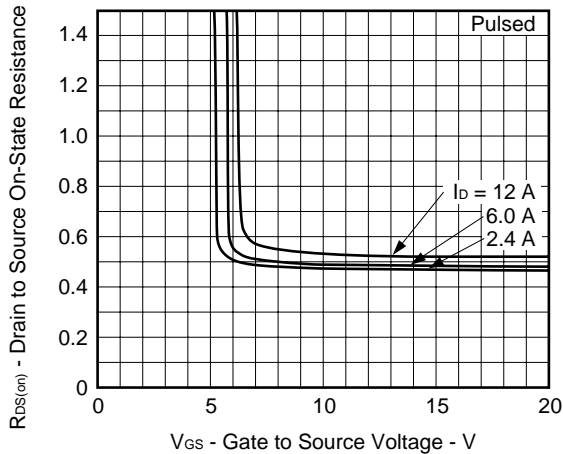
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



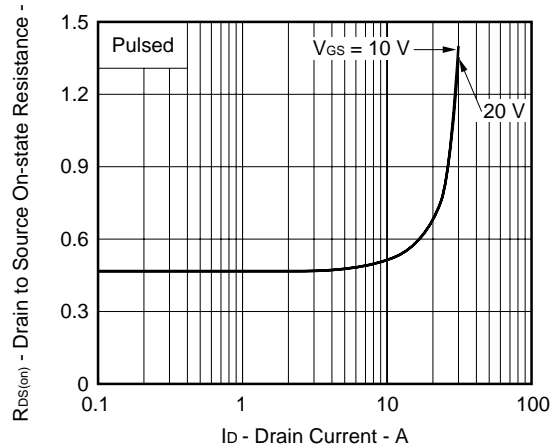
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

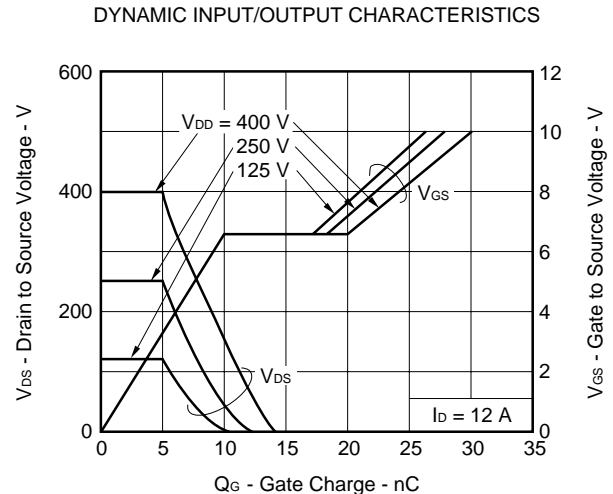
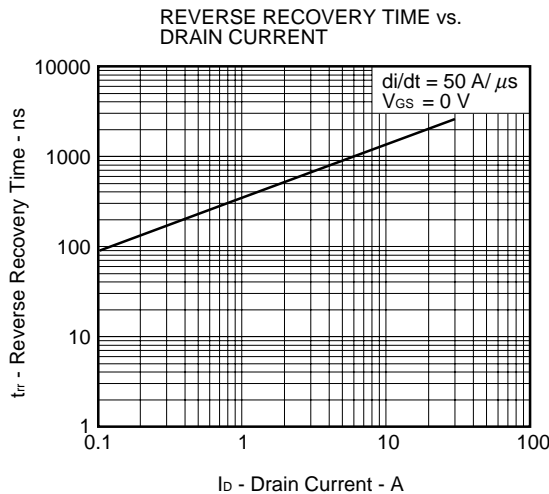
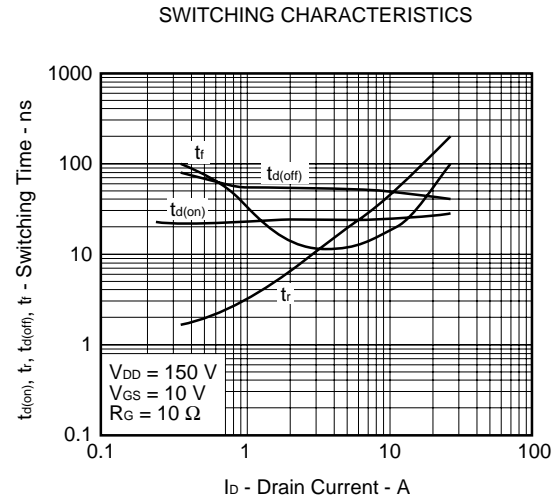
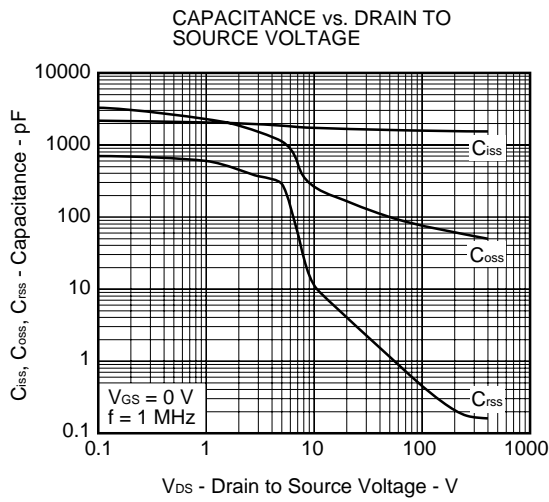
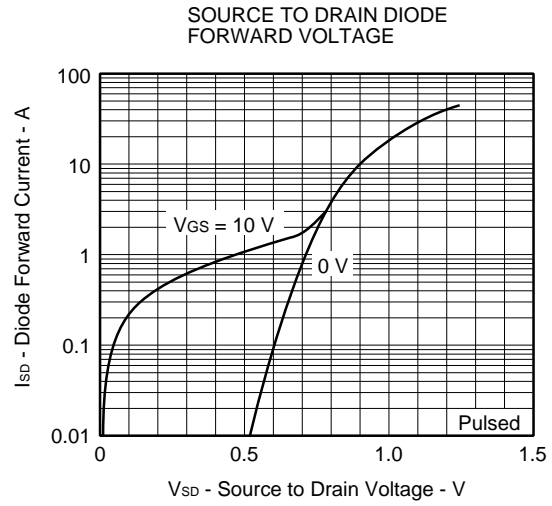
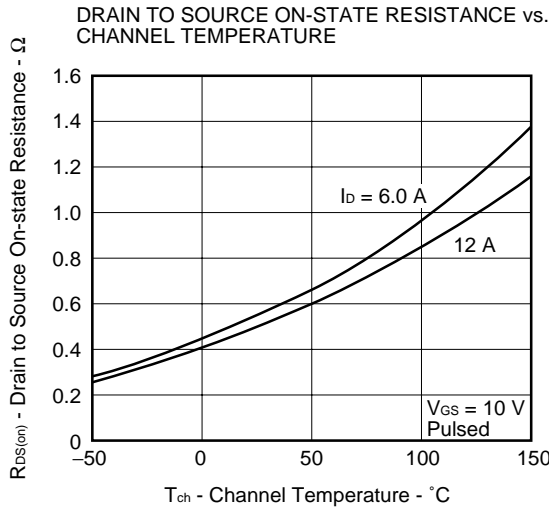


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

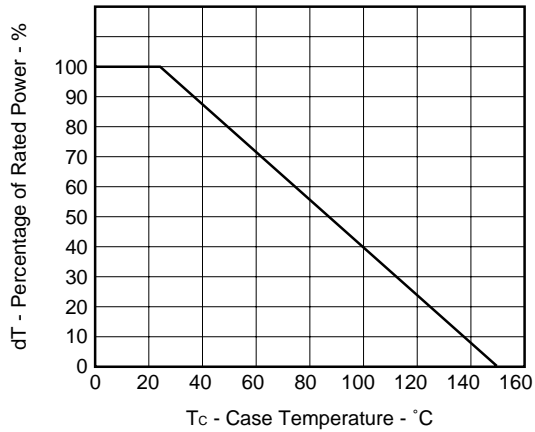


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

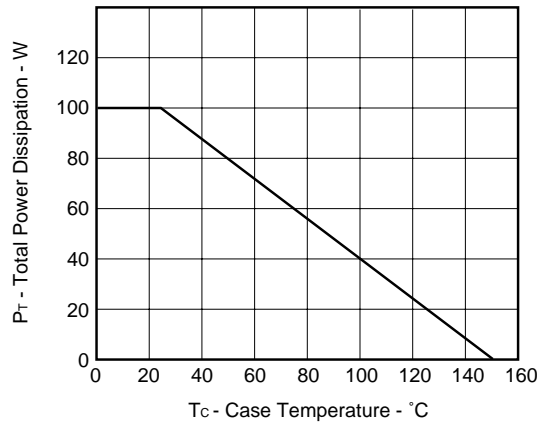




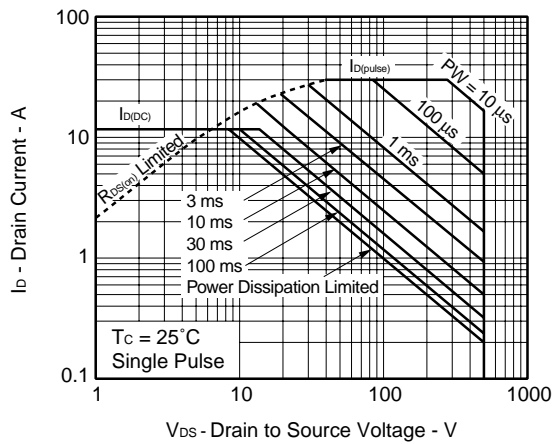
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



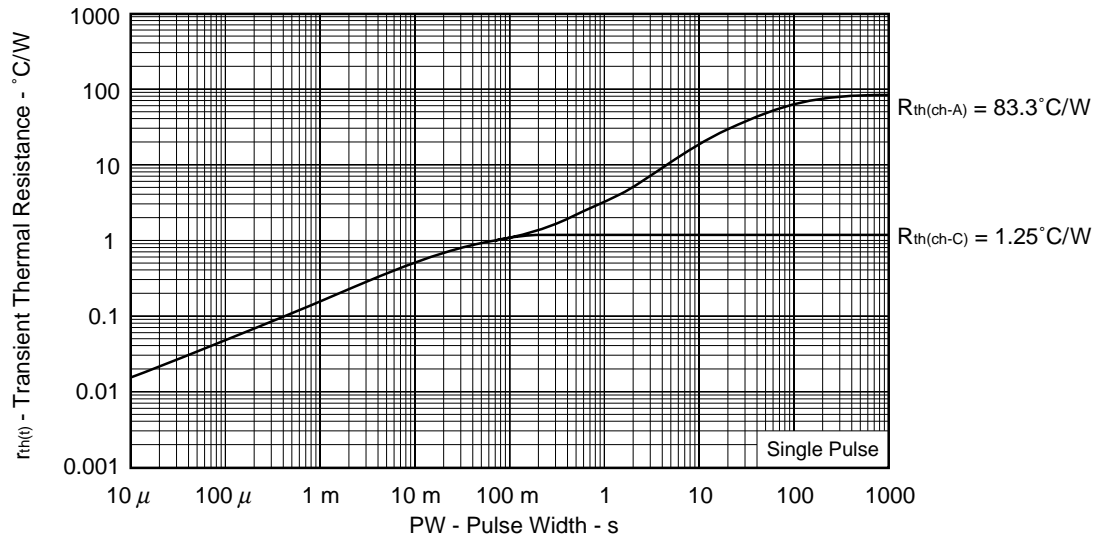
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



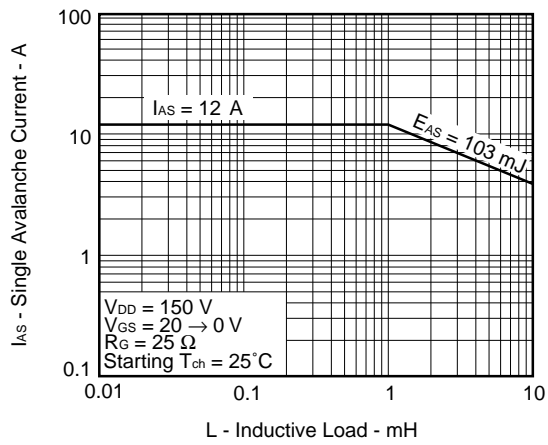
FORWARD BIAS SAFE OPERATING AREA



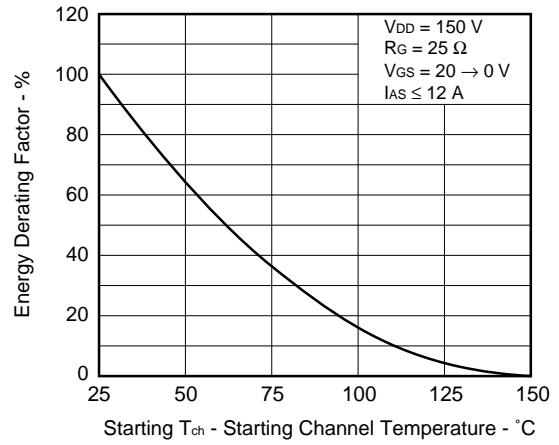
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD

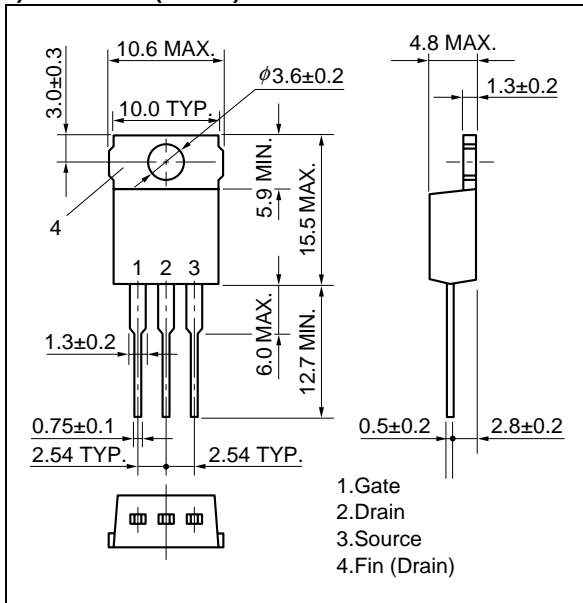


SINGLE AVALANCHE ENERGY DERATING FACTOR

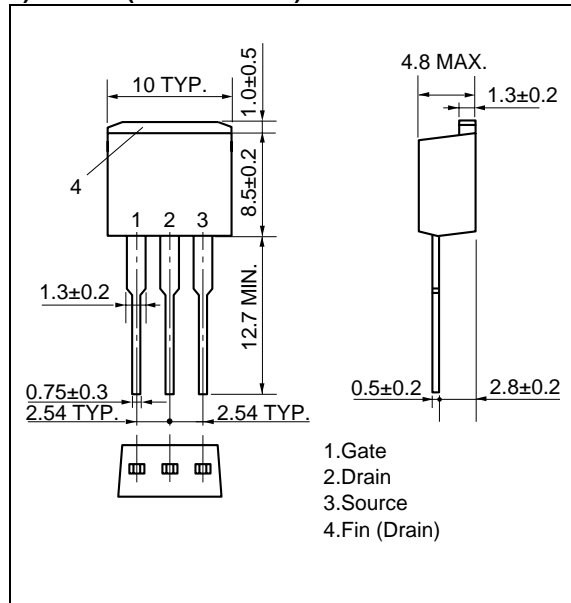


PACKAGE DRAWINGS (Unit: mm)

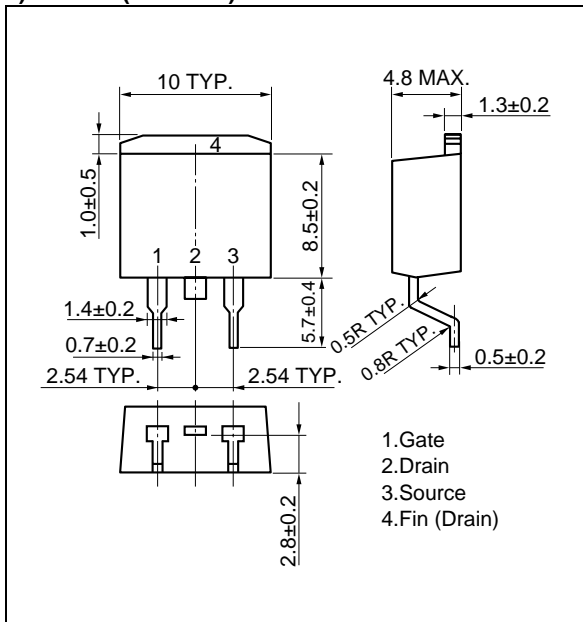
1) TO-220AB (MP-25)



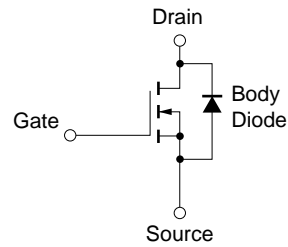
2) TO-262 (MP-25 Fin Cut)



3) TO-263 (MP-25ZJ)



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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